

/ Descriptions

SOT-23 N MOS N- CHANNEL MOSFET in a SOT-23 Plastic Package.

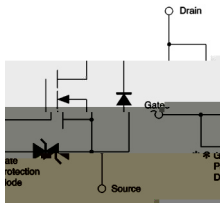
/ Features

500V HBM
Low on-resistance, fast switching speed, low voltage drive, easily designed drive circuits, easy to parallel. ESD protected up to 500V HBM .

/ Applications

Interfacing, switching.

/ Equivalent Circuit



/ Pinning



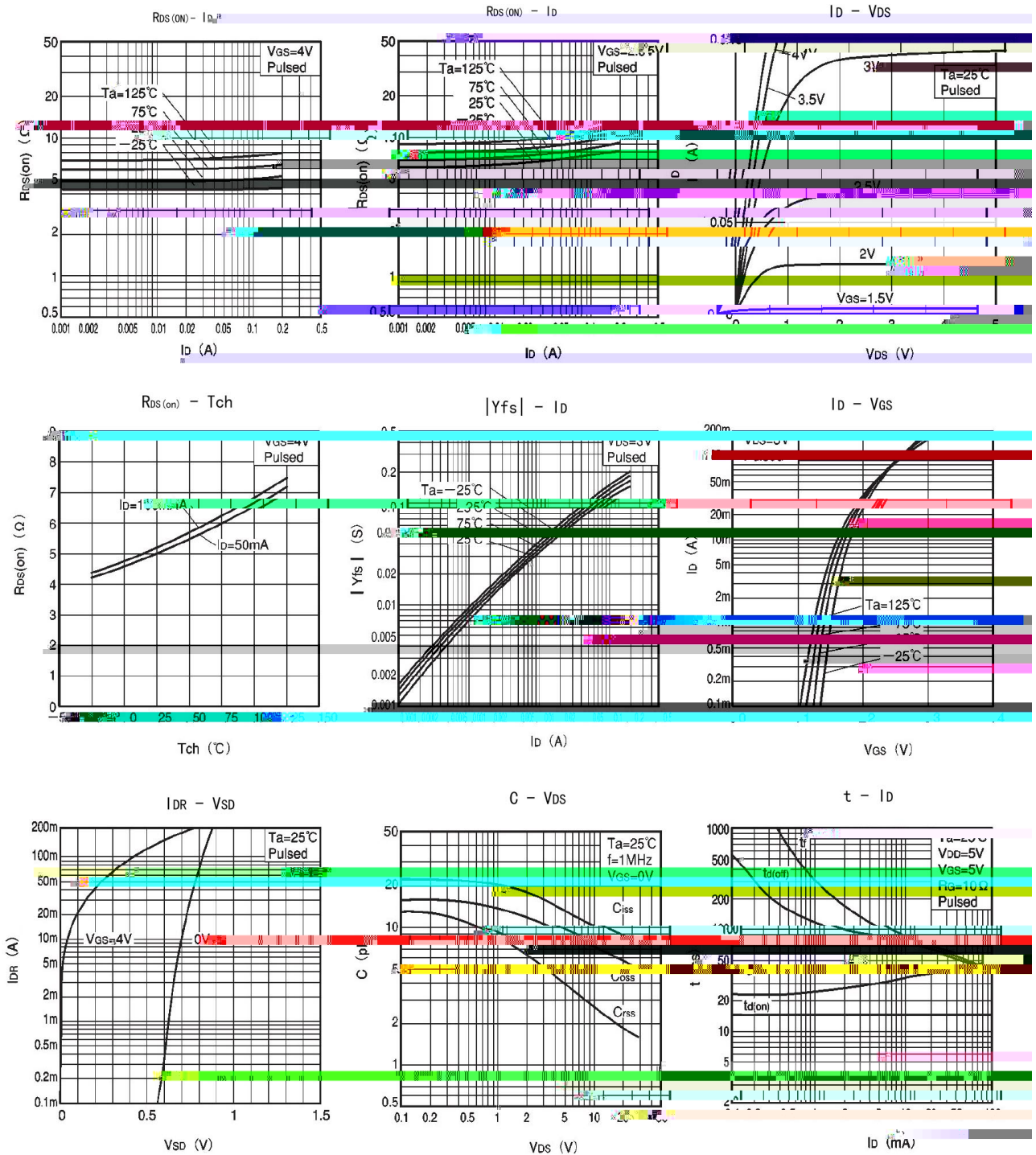
PIN1 G PIN 2 S PIN 3 D

/ Marking

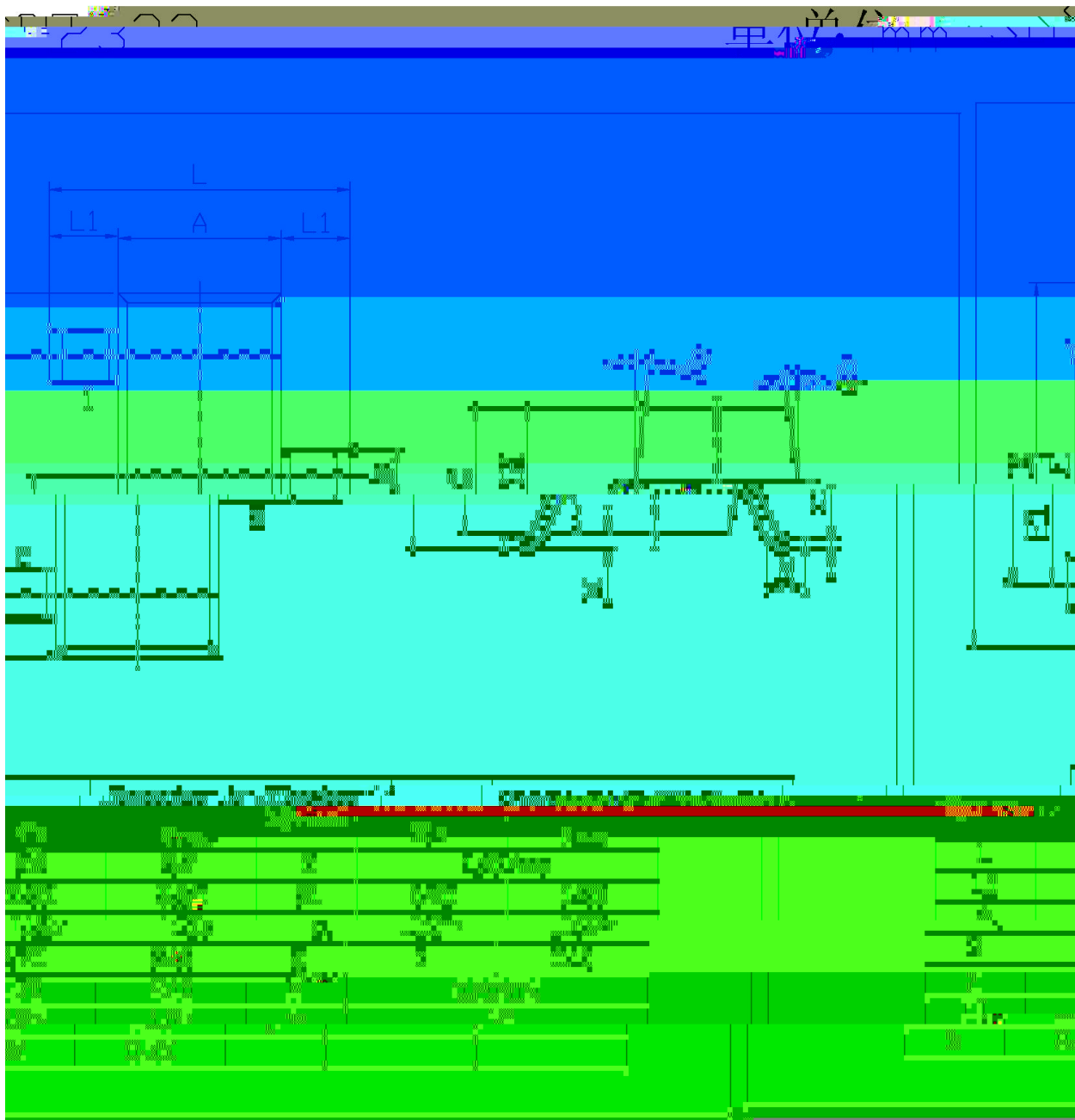
Marking	KL
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Parameter	Symbol	Rating	Unit
Drain-Source Voltage	V_{DSS}	30	V
Gate-Source Voltage	V_{GSS}	± 20	V
Drain Current – Continuous	I_D	100	mA
Drain Current- Pulsed	I_{DP}^{*1}	400	mA
Reverse Drain Current – Continuous	I_{DR}	100	mA
Reverse Drain Current –Pulsed	I_{DRP}^{*1}	200	mA
Total Power Dissipation	P_D^{*2}		

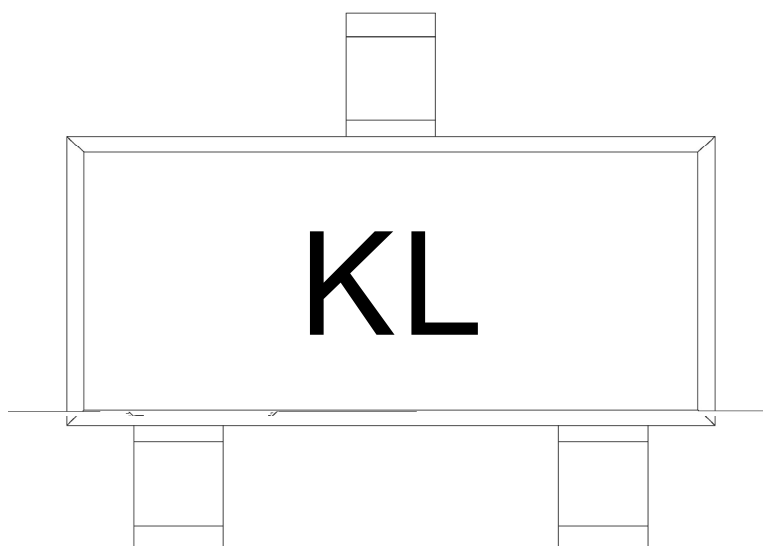
/ Electrical Characteristic Curve



/ Package Dimensions



/ Marking Instructions

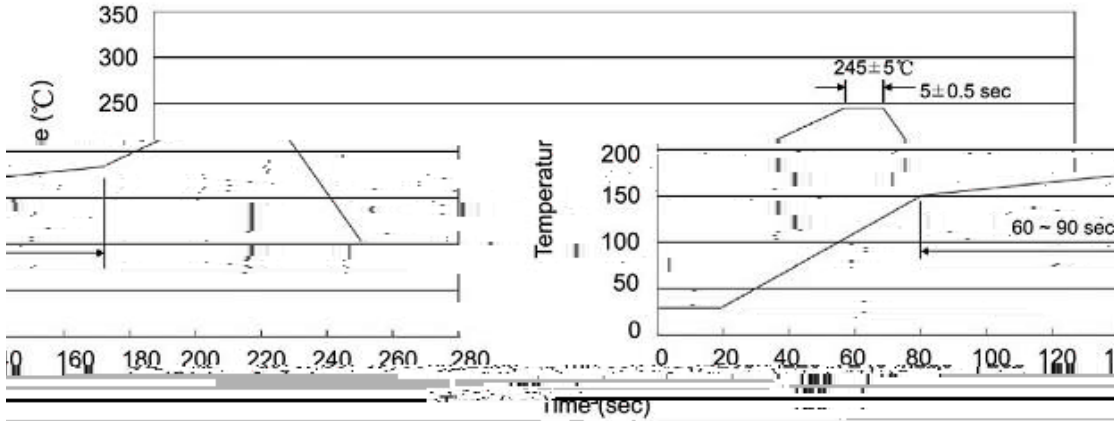


KL:

Note:

KL Package Type

() / Temperature Profile for IR Reflow Soldering (Pb-Free)



Note:

- | | | | | | |
|---|-------|-----|-------|----------|---|
| 1 | 150 | 180 | 60 | 90sec; | 1.Preheating:150~180 , Time:60~90sec. |
| 2 | 245±5 | | 5±0.5 | sec; | 2.Peak Temp.:245±5 , Duration:5±0.5sec. |
| 3 | | | 2 | 10 /sec. | 3. Cooling Speed: 2~10 /sec. |

/ Resistance to Soldering Heat Test Conditions

260±5 10±1 sec. Temp.:260±5 Time:10±1 sec

/ Packaging SPEC.

/ REEL

Package Type 封装形式	Units 包装数量					Dimension 包装尺寸 (unit: mm ³)		
	只卷盘	卷盘盒	只盒	盒箱	只箱		盒	箱

/ Notices